

Notice of References Cited

Application/Control No.

09/989,850

Applicant(s)/Patent Under

Reexamination

ABADEER ET AL

Examiner

Dao H Nguyen

Art Unit

2818

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,441,396	08-2002	Adams et al.	257/48
*	B	US-5,841,182	11-1998	Linn et al.	257/532
*	C	US-5,311,051	05-1994	Tukizi, Masaru	257/409
*	D	US-5,285,101	02-1994	Kikuchi, Hiroaki	257/593
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.

BUR920010031Us1

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,124,143	9/2000	Sugasawara			
	6,114,182	9/2000	Tabara			
	5,903,012	5/1999	Boerstler			
	5,872,449	2/1999	Gouravaram et al.			
	5,867,033	2/1999	Sporck et al.			
	5,846,848	12/1998	Chih-Sheng et al.			
	5,831,446	11/1998	So et al.			
	5,798,649	8/1998	Smayling et al.			
	5,666,049	9/1997	Yamada et al.			
	5,654,895	8/1997	Bach et al.			
	5,561,373	10/1996	Itoh			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Hirth et al., THEORY OF DISLOCATIONS, John Wiley & Sons Publishers, Second Edition
		P.G. Neudeck et al., BREAKDOWN DEGRADATION ASSOCIATED WITH ELEMENTARY SCREW DISLOCATIONS IN 4H-SiC p+n JUNCTION RECTIFIERS, SOLID STATE ELECTRONICS, Vol. 42, No 12, 1998, pp. 2157-2164

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
BUR920010031051

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,448,513	9/1995	Hu et al.			
	5,418,738	5/1995	Abadeer et al.			
	5,898,629	4/1999	Beffa et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Sato et al., DEGRADATION OF DIELECTRIC BREAKDOWN FIELD OF THERMAL SiO ₂ FILMS DUE TO STRUCTURAL DEFECTS IN CZOCHRALSKI SILICON SUBSTRATES, J. Appl. Phys. 79 (10), 15 May 1996, pp. 7944-7957
		H. Miura et al., NEW MECHANICAL RELIABILITY ISSUES FOR DEEP SUBMICRON DEVICES, IEEE Semiconductor Manufacturing Technology Workshop, (Cat. No. 98EX133), 1998, pp. 140-147

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
BUR920010031Us1

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			H. Miura et al., MECHANICAL STRESS SIMULATION DURING GATE FORMATION OF MOS DEVICES CONSIDERING CRYSTALLIZATION INDUCED STRESS OF PHOSPHORUS DOPED SILICON THIN FILMS, Journal of Microelectronics, (UK), Vol. 26, No. 2-3, March 1995, pp. 249-253
			H. Miura et al., MECHANICAL STRESS SIMULATION FOR HIGHLY RELIABLE DEEP SUBMICRON DEVICES, IEICE Trans. Electron. (Japan), Inst. Electron. Inf. & Commun. Eng., Vol. E82-C, No. 6, June 1999, pp. 830-838

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION*(Use several sheets if necessary)*ATTY DOCKET NO.
BUR920010031Us1

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			S. Wang et al., MOS TRANSISTOR WITH HIGH LEAKAGE FAILURE CAUSED BY LOCOS DISLOCATION, Semiconductor Manufacturing Technology Workshop, Taiwan Semicond. Manuf. Company, Hsinchu, Taiwan, October 1996, pp. 22-23
			S. H. Voldman et al., TLM: A TRENCH LEAKAGE MONITOR FOR A FOUR MEGABIT SPT DRAM TECHNOLOGY, IBM, Burlington, Technical Report, TR 19.90539, July 1990

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.

BUR920010031US

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			M. Noguchi et al., 0.29 μm^2 TRENCH CELL TECHNOLOGIES FOR 1 Gbit DRAMs WITH OPEN/FOLDED BIT-LANE LAYOUT AND SELECTIVE GROWTH TECHNIQUE, 1995 Symposium on VLSI Technology Digest of Technical Papers
			P. Bakeman et al., A HIGH PERFORMANCE 16-Mbit DRAM TECHNOLOGY, 1990 Symposium on VLSI Technology Digest of Technical Papers

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

BUR920010031USA

Application Number

Applicant(s)

Wagdi W. Abadeer et al.

Filing Date

Group Art Unit

*EXAMINER

INITIAL

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

T. Pompl et al., INVESTIGATION OF ULTRA-THIN GATE OXIDE RELIABILITY BEHAVIOR BY SEPARATE CHARACTERIZATION OF SOFT BREAKDOWN AND HARD BREAKDOWN, Proceedings of the International Reliability Physics Symposium, San Jose CA, April 10-13, 2000, pp. 40-47

EXAMINER

DATE CONSIDERED

***EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.